

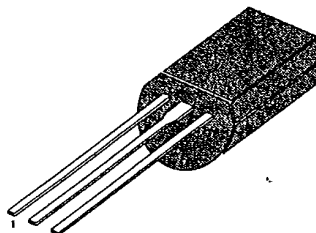
KSC2383**NPN EPITAXIAL SILICON TRANSISTOR**

COLOR TV AUDIO OUTPUT
COLOR TV VERTICAL DEFLECTION OUTPUT

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	160	V
Collector-Emitter Voltage	V_{CE0}	160	V
Emitter-Base Voltage	V_{EB0}	6	V
Collector Current	I_C	1	A
Base Current	I_B	0.5	A
Collector Dissipation	P_C	900	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

TO-92L



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

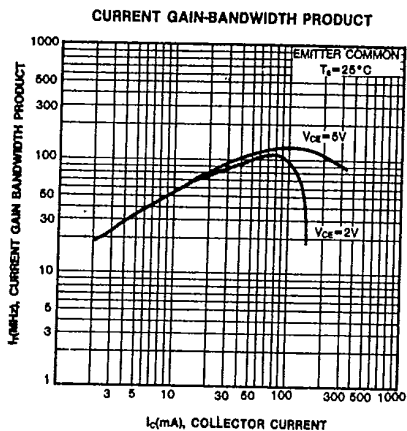
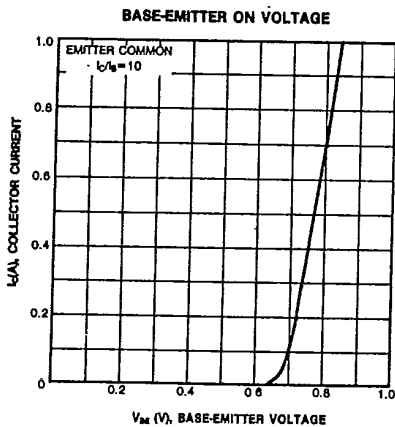
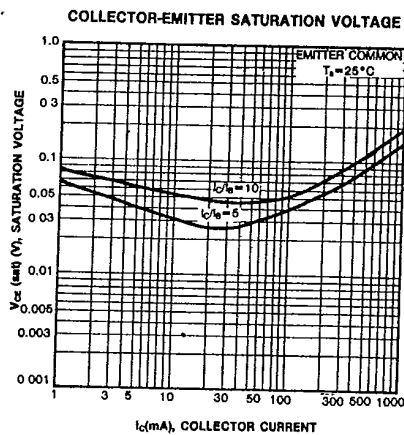
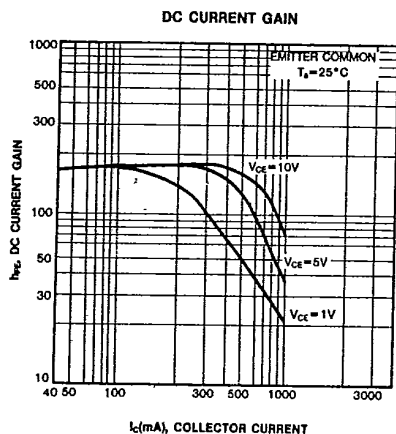
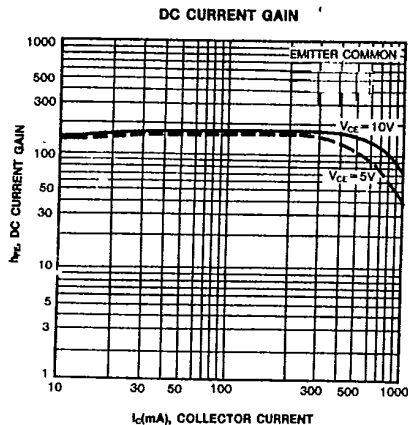
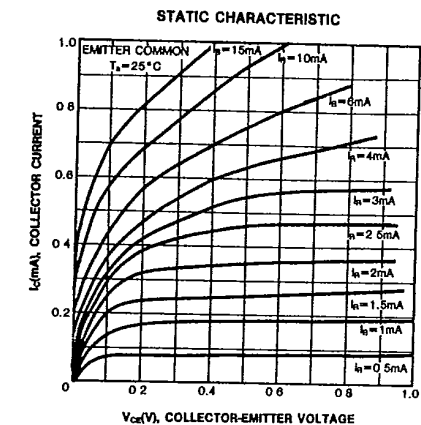
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 150\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$			1	μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 10\text{mA}, I_B = 0$	160			V
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 200\text{mA}$	60		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = 5\text{V}, I_C = 5\text{mA}$	0.45		0.75	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 5\text{V}, I_C = 200\text{mA}$	20	100		MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$			20	pF

 h_{FE} CLASSIFICATION

Classification	R	O	Y
h_{FE}	60-120	100-200	160-320

KSC2383

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3

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